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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of	:	Customer Number: 20277
Tetsuzo UEDA, et al.	:	Confirmation Number: 1264
Serial No.: 10/812,416	:	Group Art Unit: 2811
Filed: March 30, 2004	:	Examiner:
For:	:	
A 4H-POLYTYPE GALLIUM NITRIDE-BASED SEMICONDUCTOR DEVICE ON A 4H-POLYTYPE SUBSTRATE		

INFORMATION DISCLOSURE STATEMENT

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

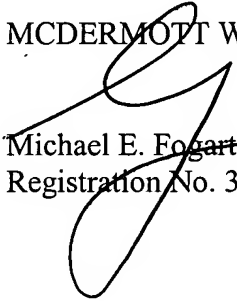
This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

10/812,416

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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SHEET 1 OF 1

INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION

(PTO-1449)

ATTY. DOCKET NO.
43890-673SERIAL NO.
10/812,416APPLICANT
Tetsuzo UEDA, et al.FILING DATE
March 30, 2004GROUP
2811

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US			
		US			
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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number 4 -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		ONOJIMA, Norio., et al. "Growth of AlN (1120) on 6H-SiC (1120) by Molecular Epitaxy." Jpn J. Appl. Phys. Vol. 41 (2002) pp. L 1348-1350
		ONOJIMA, Norio., et al. "Epitaxial Growth of AlN on 6H-SiC 91120) by Molecular-Beam Epitaxy and Effect of Low-Temperature Buffer Layer." Materials Research Society Symposium Proceedings Volume 743 (2003) L3.21.1-L3.21.6
		N. ONOJIMA., et al. "Growth of high-quality non-polar AlN on 4H-SiC(11-20) substrate by molecular-beam epitaxy." Technical Digest of 5th International Conference on Nitride Semiconductors May 25-30, 2003 Nara, Japan, P.229
		N. ONOJIMA., et al. "Extended Abstract of 2003 Fall Meeting of the Japan Society of Applied Physics Society, 30p-G-10
		N. ONOJIMA., et al. "Growth of high-quality non-polar AlN on 4H-SiC(11-20) substrate by molecular-beam epitaxy." Phys.Stat. Sol. © 0, No.7, 2502-2505 (2003)
		N. ONOJIMA., et al. "4H-polytype AlN grown on 4H-SiC (1120) substrate by polytype replication." Applied Physics Letters, Volume 83, Number 25, December 22, 2003, pp. 5208-5210

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.